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# Joint ICTP-IAEA Workshop on Physics of Radiation Effect and its Simulation for Non-Metallic Condensed Matter | (smr 2359)

## Wednesday 15 August 2012

### **Modeling of damage in ion irradiated semiconductors - Adriatico Guest House Kastler Lecture Hall (09:00-10:30)**

*The IBIC technique, expounded in previous lectures, is non destructive if very low fluences of light ions are used. However, if this condition is not fulfilled, a localized damage is induced in the semiconductor, which degrades the performances of the device. Accordingly, ions can be used both to generate recombination or trapping centres and to probe their effects on the transport properties of the material.*

*This lecture intends to illustrate an effective experimental protocol for the evaluation of the radiation induced degradation of the electronic performances of devices based on the IBIC technique and the relevant physical model, which is suitable to extract information on the effective radiation hardness of semiconductor materials.*

time	title	presenter
09:00	Modeling of damage in ion irradiated semiconductors	ETTORE VITTONI